



Express Mail No. EV 346 794 353 US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Bruno GHYSELEN et al.

Confirmation No.2491

Application No.: 10/784,017

Group Art Unit: 2822

Filing Date: February 20, 2004

Examiner: B.H. Au

For: METHOD FOR FORMING A RELAXED OR
PSEUDO-RELAXED USEFUL LAYER ON A
SUBSTRATE

Atty. Docket No.: 4717-10200

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Pursuant to applicants' duty of disclosure under 37 C.F.R. 1.56, enclosed are copies of four additional references for the Examiner's review and consideration. These references are listed on the enclosed Form PTO-1449. It is respectfully requested that these references be made of record in this application by the Examiner's completion and return of the PTO Form 1449.

The fee which is believed to be due for this submission is \$180. Please charge any and all fees for processing this statement and the amendment being filed concurrently herewith to **Winston & Strawn LLP** Deposit Account No. 50-1814.

Respectfully submitted,

11/18/05

Date

Allan A. Fanucci

(Reg. No. 30,256)

WINSTON & STRAWN LLP
Customer No. 28765

212-294-3311



LIST OF REFERENCES CITED BY APPLICANT
(Use several sheets if necessary)

ATTY. DOCKET NO.:	APPLICATION NO.:
4717-10200	10/784,017
APPLICANT:	
Bruno GHYSELEN et al.	
FILING DATE:	GROUP:
February 20, 2004	2822

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	2003/0013305 A1	1/2003	Sugii et al.	438	689	
	AB	6,059,895	5/2000	Chu et al.	148	33.1	
	AC	6,100,166	8/2000	Sakaguchi et al.	438	455	
	AD						
	AE						
	AF						
	AG						
	A1						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AJ	WO02/43153	5/2002	PCT (Abstract)			X	
	AK							
	AL							

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

	AM	
	AN	
	AO	
	AP	
	AQ	

EXAMINER	DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

LIST OF REFERENCES CITED BY APPLICANT <i>(Use several sheets if necessary)</i>	ATTY. DOCKET NO.:	APPLICATION NO.:
	4717-10200	10/784,017
	APPLICANT:	
	Bruno GHYSELEN et al.	
FILING DATE:	GROUP:	
February 20, 2004	2822	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	5,461,243	10/1995	Ek et al.	257	190	
	AB	6,352,942 B1	3/2002	Luan et al.	438	770	
	AC	2002/0072130	6/2002	Cheng et al.	438	10	
	AD						
	AE						
	AF						
	AG						
	A1						

FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
	AJ						
	AK						
	AL						

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)							
---	--	--	--	--	--	--	--

	AM	B. Holländer et al., "Strain relaxation of pseudomorphic Si _{1-x} Ge _x /Si(100) heterostructures after hydrogen or helium ion implantation for virtual substrate fabrication", Nuclear Instruments and Methods in Physics Research B 175-177 (2001) 357-367 (2001)
	AN	K.D. Hobart et al. "Complaint Substrates: A Comparative Study of the Relaxation Mechanisms of Strained Films Bonded to High and Low Viscosity Oxides", Electronic Materials, Vol. 29, No. 7, pp. 897-900 (2000)
	AO	Friedrich Schäffler, "High-mobility Si and Ge structures", Semicond. Sci. Technol., Vol. 12, pp. 1515-1548 (1997)
	AP	Q. Y. Tong et al "Extracts of "Semi-conductor on wafer bonding", Science and Technology, Interscience Technology, Wiley Interscience publication, Johnson Wiley & Sons, Inc.
	AQ	J.P. Collinge, "Silicon-on-insulator technology", Materials to VLSI, 2nd Edition", Kluwer Academic Publisher, pp. 50-51.

EXAMINER	DATE CONSIDERED
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

LIST OF REFERENCES CITED BY APPLICANT <i>(Use several sheets if necessary)</i>	ATTY. DOCKET NO.:	APPLICATION NO.:
	4717-10200	10/784,017
	APPLICANT:	
	Bruno GHYSELEN et al.	
FILING DATE: February 20, 2004	GROUP:	
	2822	

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	5,882,987	3/1999	Sirikrishnan	438	458	
	AB	5,906,951	5/1999	Chu et al.	438	751	
	AC	6,524,935	2/2003	Canaperi et al.	438	478	
	AD	6,573,126 B2	6/2003	Cheng et al.	438	149	
	AE	6,633,066 B1	10/2003	Bae et al.	257	347	
	AF	2003/0003679 A1	6/2003	Doyle et al.	438	406	
	AG	2003/0155568 A1	8/2003	Cheng et al.	257	12	
	A1	2003/0168654 A1	9/2003	Cheng et al.	257	19	

FOREIGN PATENT DOCUMENTS

AH

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AJ	EP 1 248 294 A2	10/2002	Europe			X	
	AK	FR 2 818 010 (with English Abstract)	8/2002	France			X	
	AL	DE 101 00 194 A1	6/2001	Germany			X	
	AM	WO 02/15244 A2	2/2002	PCT			X	
	AN	WO 02/47156 A1	2/2002	PCT			X	
	AO	WO 99/53539	10/1999	PCT			X	

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

AP	T. Tezuka et al., XP001109835, High-Performance Strained Si-on-Insulator MOSFETs by Novel Fabrication Processes Utilizing Ge-Condensation Technique, Symposium On VLSI Tech., Digest of Technical Papers. Honolulu, NY:IEEE US, pp. 96-97 (2002)
AQ	S. Mantl et al., "Strain relaxation of epitaxial SGe layers on Si(100) improved by hydrogen implantation" Nuclear Instruments and Methods in Physics Research , Vol. 47, No. 1-4, pp. 29-34 (1999)

EXAMINER	DATE CONSIDERED
----------	-----------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.